

# steven Denbaars

## List of Publications by Citations

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973  
papers

45,901  
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103  
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177  
g-index

1,040  
ext. papers

49,715  
ext. citations

3  
avg, IF

7.24  
L-index

#	Paper	IF	Citations
973	Direct formation of quantum-sized dots from uniform coherent islands of InGaAs on GaAs surfaces. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 3203-3205	3.3	1403
972	Increase in the extraction efficiency of GaN-based light-emitting diodes via surface roughening. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 855-857	3.3	1054
971	Polarization effects, surface states, and the source of electrons in AlGaIn/GaN heterostructure field effect transistors. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 250-252	3.3	747
970	Role of threading dislocation structure on the x-ray diffraction peak widths in epitaxial GaN films. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 643-645	3.3	719
969	B-shaped temperature-dependent emission shift and carrier dynamics in InGaIn/GaN multiple quantum wells. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 1370-1372	3.3	568
968	Absorption coefficient, energy gap, exciton binding energy, and recombination lifetime of GaN obtained from transmission measurements. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 2572-2574	3.3	564
967	Origin of defect-insensitive emission probability in In-containing (Al,In,Ga)N alloy semiconductors. <i>Nature Materials</i> , <b>2006</b> , 5, 810-6	26.5	547
966	Structural characterization of nonpolar (112 0) a-plane GaN thin films grown on (11 02) r-plane sapphire. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 469-471	3.3	431
965	Structural origin of V-defects and correlation with localized excitonic centers in InGaIn/GaN multiple quantum wells. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 692-694	3.3	369
964	Effective band gap inhomogeneity and piezoelectric field in InGaIn/GaN multiquantum well structures. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 2006-2008	3.3	363
963	Defect structure of metal-organic chemical vapor deposition-grown epitaxial (0001) GaN/Al <sub>2</sub> O <sub>3</sub> . <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 3228-3237	2.4	350
962	Homoepitaxial growth of GaN under Ga-stable and N-stable conditions by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>1997</b> , 82, 5472-5479	2.4	339
961	High quantum efficiency InGaIn/GaN solar cells with 2.95 eV band gap. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 143502	3.3	333
960	High-power AlGaIn/GaN HEMTs for Ka-band applications. <i>IEEE Electron Device Letters</i> , <b>2005</b> , 26, 781-783	4.1	299
959	Dislocation mediated surface morphology of GaN. <i>Journal of Applied Physics</i> , <b>1999</b> , 85, 6470-6476	2.4	321
958	AlGaIn/AlN/GaN high-power microwave HEMT. <i>IEEE Electron Device Letters</i> , <b>2001</b> , 22, 457-459	4.1	303
957	Polarization-induced charge and electron mobility in AlGaIn/GaN heterostructures grown by plasma-assisted molecular-beam epitaxy. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 4520-4526	2.4	317

956	High Breakdown Voltage Achieved on AlGaIn/GaN HEMTs With Integrated Slant Field Plates. <i>IEEE Electron Device Letters</i> , <b>2006</b> , 27, 713-715	4.1	282
955	Electrical characterization of GaN p-n junctions with and without threading dislocations. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 975-977	3.3	296
954	Very high breakdown voltage and large transconductance realized on GaN heterojunction field effect transistors. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 1438-1440	3.3	289
953	Growth of Fe doped semi-insulating GaN by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 439-441	3.3	289
952	Heavy doping effects in Mg-doped GaN. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 1832-1835	2.4	278
951	Semipolar $\bar{\Gamma}$ InGaIn/GaN Light-Emitting Diodes for High-Efficiency Solid-State Lighting. <i>Journal of Display Technology</i> , <b>2013</b> , 9, 190-198		277
950	Development of gallium-nitride-based light-emitting diodes (LEDs) and laser diodes for energy-efficient lighting and displays. <i>Acta Materialia</i> , <b>2013</b> , 61, 945-951	8.3	279
949	Structural evolution in epitaxial metalorganic chemical vapor deposition grown GaN films on sapphire. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 1541-1543	3.3	273
948	Efficient and color-tunable oxyfluoride solid solution phosphors for solid-state white lighting. <i>Advanced Materials</i> , <b>2011</b> , 23, 2300-5	23.6	276
947	High-performance (Al,Ga)N-based solar-blind ultraviolet p $\bar{\Gamma}$ detectors on laterally epitaxially overgrown GaN. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 247-249	3.3	263
946	Coupling of InGaIn quantum-well photoluminescence to silver surface plasmons. <i>Physical Review B</i> , <b>1999</b> , 60, 11564-11567	3.3	266
945	Consequences of Optimal Bond Valence on Structural Rigidity and Improved Luminescence Properties in Sr <sub>x</sub> Ba <sub>2-x</sub> SiO <sub>4</sub> :Eu <sup>2+</sup> Orthosilicate Phosphors. <i>Chemistry of Materials</i> , <b>2014</b> , 26, 2275-2282	9.5	259
944	AlN/GaN and (Al,Ga)N/AlN/GaN two-dimensional electron gas structures grown by plasma-assisted molecular-beam epitaxy. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 5196-5201	2.4	236
943	Influence of sapphire nitridation on properties of gallium nitride grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 1525-1527	3.3	230
942	Enhanced Mg doping efficiency in Al <sub>0.2</sub> Ga <sub>0.8</sub> N/GaN superlattices. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 3681-3683	3.3	230
941	Scanning capacitance microscopy imaging of threading dislocations in GaN films grown on (0001) sapphire by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 2247-2249	3.3	218
940	Materials and growth issues for high-performance nonpolar and semipolar light-emitting devices. <i>Semiconductor Science and Technology</i> , <b>2012</b> , 27, 024001	1.7	205
939	High Power and High External Efficiency m-Plane InGaIn Light Emitting Diodes. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L126-L128	1.3	219

938	High Al-content AlGaIn/GaN MODFETs for ultrahigh performance. <i>IEEE Electron Device Letters</i> , <b>1998</b> , 19, 50-53	4.1	203
937	Microstructure of GaN laterally overgrown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 747-749	3.3	214
936	Sr <sub>2</sub> .975Ba <sub>x</sub> Ce <sub>0.025</sub> AlO <sub>4</sub> F: a Highly Efficient Green-Emitting Oxyfluoride Phosphor for Solid State White Lighting. <i>Chemistry of Materials</i> , <b>2010</b> , 22, 2842-2849	9.5	200
935	High breakdown GaN HEMT with overlapping gate structure. <i>IEEE Electron Device Letters</i> , <b>2000</b> , 21, 421-423	4.2	189
934	Nonpolar and Semipolar III-Nitride Light-Emitting Diodes: Achievements and Challenges. <i>IEEE Transactions on Electron Devices</i> , <b>2010</b> , 57, 88-100	2.7	194
933	Nucleation layer evolution in metal-organic chemical vapor deposition grown GaN. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 1371-1373	3.3	189
932	High-brightness polarized light-emitting diodes. <i>Light: Science and Applications</i> , <b>2012</b> , 1, e22-e22	16.2	188
931	Demonstration of a semipolar (101̄̄̄) InGaIn/GaN green light emitting diode. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 231110	3.3	182
930	Indium tin oxide contacts to gallium nitride optoelectronic devices. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 3930-3932	3.3	180
929	Demonstration of Nonpolar-m-Plane InGaIn/GaN Laser Diodes. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L190-L191	1.3	180
928	Nonpolar InGaIn/GaN emitters on reduced-defect lateral epitaxially overgrown a-plane GaN with drive-current-independent electroluminescence emission peak. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 5143-5145	3.2	177
927	Robust thermal performance of Sr <sub>2</sub> Si <sub>5</sub> N <sub>8</sub> :Eu <sup>2+</sup> : An efficient red emitting phosphor for light emitting diode based white lighting. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 241106	3.3	178
926	GaN microwave electronics. <i>IEEE Transactions on Microwave Theory and Techniques</i> , <b>1998</b> , 46, 756-761	3.7	164
925	LaSr <sub>2</sub> AlO <sub>5</sub> , a Versatile Host Compound for Ce <sup>3+</sup> -Based Yellow Phosphors: Structural Tuning of Optical Properties and Use in Solid-State White Lighting. <i>Chemistry of Materials</i> , <b>2009</b> , 21, 2957-2966	9.5	170
924	Spin coherence and dephasing in GaN. <i>Physical Review B</i> , <b>2001</b> , 63,	3.3	168
923	Crystallographic orientation dependence of dopant and impurity incorporation in GaN films grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 3817-3823	1.6	167
922	Demonstration of Nonpolar-m-Plane InGaIn/GaN Light-Emitting Diodes on Free-Standing-m-Plane GaN Substrates. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L173-L175	1.3	162
921	Photonic-crystal GaN light-emitting diodes with tailored guided modes distribution. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 061124	3.3	156

920	Measurement of electron overflow in 450 nm InGaN light-emitting diode structures. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 061116	3-3	161
919	Defect reduction in (112 0) a-plane gallium nitride via lateral epitaxial overgrowth by hydride vapor-phase epitaxy. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 644-646	3-3	162
918	White light from InGaN/conjugated polymer hybrid light-emitting diodes. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 2664-2666	3-3	160
917	High-Power Blue-Violet Semipolar ( $2\bar{1}1$ ) InGaN/GaN Light-Emitting Diodes with Low Efficiency Droop at 200 A/cm <sup>2</sup> . <i>Applied Physics Express</i> , <b>2011</b> , 4, 082104	2-3	154
916	High internal and external quantum efficiency InGaN/GaN solar cells. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 021102	3-3	151
915	Metalorganic chemical vapor deposition of GaN on Si(111): Stress control and application to field-effect transistors. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 7846-7851	2-4	155
914	Low interface trap density for remote plasma deposited SiO <sub>2</sub> on n-type GaN. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 1850-1852	3-3	147
913	Optical properties of yellow light-emitting diodes grown on semipolar (112 $\bar{1}$ ) bulk GaN substrates. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 221110	3-3	145
912	A yellow-emitting Ce <sup>3+</sup> phosphor, La <sub>1-x</sub> Ce <sub>x</sub> Sr <sub>2</sub> AlO <sub>5</sub> , for white light-emitting diodes. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 091905	3-3	147
911	Threading dislocation reduction via laterally overgrown nonpolar (112 0) a-plane GaN. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 1201-1203	3-3	146
910	Emission mechanisms of bulk GaN and InGaN quantum wells prepared by lateral epitaxial overgrowth. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 1460-1462	3-3	142
909	Optical properties of InGaN quantum wells. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 59, 298-306	3-1	141
908	Indium incorporation and emission properties of nonpolar and semipolar InGaN quantum wells. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 201108	3-3	146
907	Polarization effects in AlGaN/GaN and GaN/AlGaN/GaN heterostructures. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 10114-10118	2-4	140
906	Metalorganic chemical vapor deposition of high mobility AlGaN/GaN heterostructures. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 5850-5857	2-4	138
905	Impact of carbon on trap states in n-type GaN grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 374-376	3-3	141
904	Bias dependent microwave performance of AlGaN/GaN MODFET's up to 100 V. <i>IEEE Electron Device Letters</i> , <b>1997</b> , 18, 290-292	4-1	131
903	High-Efficiency Single-Quantum-Well Green and Yellow-Green Light-Emitting Diodes on Semipolar ( $2\bar{1}1$ ) GaN Substrates. <i>Applied Physics Express</i> , <b>2010</b> , 3, 122102	2-3	136

902	Structural and morphological characteristics of planar (112 0) a-plane gallium nitride grown by hydride vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1554-1556	3.3	134
901	Influence of the dynamic access resistance in the g/sub m/ and f/sub T/ linearity of AlGaIn/GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , <b>2005</b> , 52, 2117-2123	2.7	132
900	Influence of the substrate misorientation on the properties of N-polar GaN films grown by metal organic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 083546	2.4	131
899	Realization of wide electron slabs by polarization bulk doping in graded III-V nitride semiconductor alloys. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 4395-4397	3.3	132
898	Memory Effect and Redistribution of Mg into Sequentially Regrown GaN Layer by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, 50-53	1.3	124
897	Polarization-enhanced Mg doping of AlGaIn/GaN superlattices. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 2444-2446	4.6	129
896	Advances in the LED Materials and Architectures for Energy-Saving Solid-State Lighting Toward Lighting Revolution. <i>IEEE Photonics Journal</i> , <b>2012</b> , 4, 613-619	1.7	120
895	Measured and calculated radiative lifetime and optical absorption of In <sub>x</sub> Ga <sub>1-x</sub> N/GaN quantum structures. <i>Physical Review B</i> , <b>2000</b> , 61, 10994-11008	3.3	125
894	AlGaIn/GaN current aperture vertical electron transistors with regrown channels. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 2073-2078	2.4	118
893	Impurity incorporation in heteroepitaxial N-face and Ga-face GaN films grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 1124-1131	1.6	125
892	Photonic bands in two-dimensionally patterned multimode GaN waveguides for light extraction. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 101107	3.3	124
891	Proxies from Ab Initio Calculations for Screening Efficient Ce <sup>3+</sup> Phosphor Hosts. <i>Journal of Physical Chemistry C</i> , <b>2013</b> , 117, 17955-17959	3.7	123
890	High-performance E-mode AlGaIn/GaN HEMTs. <i>IEEE Electron Device Letters</i> , <b>2006</b> , 27, 428-430	4.1	120
889	Recent progress in metal-organic chemical vapor deposition of $\left(000\bar{1}\right)$ N-polar group-III nitrides. <i>Semiconductor Science and Technology</i> , <b>2014</b> , 29, 113001	1.7	117
888	Efficient and stable laser-driven white lighting. <i>AIP Advances</i> , <b>2013</b> , 3, 072107	1.5	119
887	N-polar GaN epitaxy and high electron mobility transistors. <i>Semiconductor Science and Technology</i> , <b>2013</b> , 28, 074009	1.7	109
886	Improved electroluminescence on nonpolar m-plane InGaIn/GaN quantum wells LEDs. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2007</b> , 1, 125-127	2.4	120
885	Si doping effect on strain reduction in compressively strained Al <sub>0.49</sub> Ga <sub>0.51</sub> N thin films. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 674-676	3.3	118

884	High efficiency of III-nitride micro-light-emitting diodes by sidewall passivation using atomic layer deposition. <i>Optics Express</i> , <b>2018</b> , 26, 21324-21331	3.2	112
883	Microstructural evolution of a-plane GaN grown on a-plane SiC by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 1281-1283	3.3	113
882	Limiting factors of room-temperature nonradiative photoluminescence lifetime in polar and nonpolar GaN studied by time-resolved photoluminescence and slow positron annihilation techniques. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 021914	3.3	112
881	SIMS investigations into the effect of growth conditions on residual impurity and silicon incorporation in GaN and Al <sub>x</sub> Ga <sub>1-x</sub> N. <i>Journal of Electronic Materials</i> , <b>2000</b> , 29, 15-20	1.9	114
880	Improved quality (112̄0̄)a-plane GaN with sidewall lateral epitaxial overgrowth. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 061908	3.3	113
879	Sustained high external quantum efficiency in ultrasmall blue III-nitride micro-LEDs. <i>Applied Physics Express</i> , <b>2017</b> , 10, 032101	2.3	110
878	Defect reduction in (11̄00) m-plane gallium nitride via lateral epitaxial overgrowth by hydride vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 111917	3.3	112
877	Well-width dependence of photoluminescence emission from a-plane GaN/AlGa <sub>n</sub> multiple quantum wells. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 496-498	3.3	104
876	Optically and thermally detected deep levels in n-type Schottky and p+n GaN diodes. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 3064-3066	3.3	108
875	Group III-nitride lasers: a materials perspective. <i>Materials Today</i> , <b>2011</b> , 14, 408-415	21.5	107
874	Photonic crystal laser lift-off GaN light-emitting diodes. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 133514	3.3	104
873	Measured microwave power performance of AlGa <sub>n</sub> /GaN MODFET. <i>IEEE Electron Device Letters</i> , <b>1996</b> , 17, 455-457	4.1	102
872	Structural and optical properties of GaN laterally overgrown on Si(111) by metalorganic chemical vapor deposition using an AlN buffer layer. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , <b>1999</b> , 4, 1		103
871	High quantum efficiency InGa <sub>n</sub> /Ga <sub>n</sub> multiple quantum well solar cells with spectral response extending out to 520 nm. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 201107	3.3	100
870	Role of inclined threading dislocations in stress relaxation in mismatched layers. <i>Journal of Applied Physics</i> , <b>2005</b> , 97, 103534	2.4	99
869	Growth and characterization of N-polar InGa <sub>n</sub> /Ga <sub>n</sub> multiquantum wells. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 191908	3.3	97
868	Demonstration of a III-nitride vertical-cavity surface-emitting laser with a III-nitride tunnel junction intracavity contact. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 091105	3.3	94
867	Defect reduction in nonpolar a-plane GaN films using in situ Si <sub>n</sub> nanomask. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 041903	3.3	96

866	High-quality coalescence of laterally overgrown GaN stripes on GaN/sapphire seed layers. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 1706-1708	3.3	95
865	High luminous flux from single crystal phosphor-converted laser-based white lighting system. <i>Optics Express</i> , <b>2016</b> , 24, A215-21	3.2	96
864	Effect of threading dislocation density on Ni $\delta$ -GaN Schottky diode I-V characteristics. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 023709	2.4	94
863	Mg doping of GaN layers grown by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 718-720	3.3	97
862	Hydrogen passivation of deep levels in n-GaN. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 1499-1501	3.3	95
861	Characteristics of Indium-Gallium-Nitride Multiple-Quantum-Well Blue Laser Diodes Grown by MOCVD. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , <b>1997</b> , 2, 1		85
860	4 Gbps direct modulation of 450 nm GaN laser for high-speed visible light communication. <i>Optics Express</i> , <b>2015</b> , 23, 16232-7	3.2	93
859	A green-yellow emitting oxyfluoride solid solution phosphor Sr <sub>2</sub> Ba(AlO <sub>4</sub> F) <sub>1-x</sub> (SiO <sub>5</sub> ) <sub>x</sub> :Ce <sup>3+</sup> for thermally stable, high color rendition solid state white lighting. <i>Journal of Materials Chemistry</i> , <b>2012</b> , 22, 18204		94
858	Demonstration of Nonpolar GaN-Based Vertical-Cavity Surface-Emitting Lasers. <i>Applied Physics Express</i> , <b>2012</b> , 5, 092104	2.3	94
857	Development of Nonpolar and Semipolar InGaN/GaN Visible Light-Emitting Diodes. <i>MRS Bulletin</i> , <b>2009</b> , 34, 318-323	3	93
856	Influence of Si doping on characteristics of InGaN/GaN multiple quantum wells. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 1128-1130	3.3	92
855	Morphological and Structural Transitions in GaN Films Grown on Sapphire by Metal-Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1996</b> , 35, L1648-L1651	1.3	89
854	Partial strain relaxation via misfit dislocation generation at heterointerfaces in (Al,In)GaN epitaxial layers grown on semipolar (112 $\bar{2}$ ) GaN free standing substrates. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 251905	3.3	92
853	High power and high efficiency green light emitting diode on free-standing semipolar (11 $\bar{2}$ 2) bulk GaN substrate. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2007</b> , 1, 162-164	2.4	90
852	Mechanisms of lateral epitaxial overgrowth of gallium nitride by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>1998</b> , 195, 328-332	1.6	90
851	2 Gbit/s data transmission from an unfiltered laser-based phosphor-converted white lighting communication system. <i>Optics Express</i> , <b>2015</b> , 23, 29779-87	3.2	87
850	The Effect of Growth Environment on the Morphological and Extended Defect Evolution in GaN Grown by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, 4460-4466	1.3	87
849	Optical Properties of GaAs Confined in the Pores of MCM-41. <i>Journal of Physical Chemistry B</i> , <b>1998</b> , 102, 3341-3344	3.3	88



848	Metalorganic chemical vapor deposition growth of high optical quality and high mobility GaN. <i>Journal of Electronic Materials</i> , <b>1995</b> , 24, 1707-1709	1.9	83
847	High Brightness Violet InGaN/GaN Light Emitting Diodes on Semipolar $\{10\bar{1}0\}$ Bulk GaN Substrates. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L129-L131	1.3	84
846	High mobility two-dimensional electron gas in AlGaIn/GaN heterostructures grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 3528-3530	3.3	75
845	Microstructure and enhanced morphology of planar nonpolar m-plane GaN grown by hydride vapor phase epitaxy. <i>Journal of Electronic Materials</i> , <b>2005</b> , 34, 357-360	1.9	82
844	Hybrid tunnel junction contacts to III-nitride light-emitting diodes. <i>Applied Physics Express</i> , <b>2016</b> , 9, 022102	3	83
843	Optical and structural properties of GaN nanopillar and nanostripe arrays with embedded InGaIn/GaN multi-quantum wells. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 054314	2.4	81
842	High-Power, Low-Efficiency-Droop Semipolar $\{20\bar{2}1\}$ Single-Quantum-Well Blue Light-Emitting Diodes. <i>Applied Physics Express</i> , <b>2012</b> , 5, 062103	2.3	80
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837	High Brightness Blue InGaIn/GaN Light Emitting Diode on Nonpolar-m-plane Bulk GaN Substrate. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L960-L962	1.3	78
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826	High quality AlN grown on SiC by metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 191906	3.3	73
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145	An exploratory study of acidic ammonothermal growth in a TZM autoclave at high temperatures. <i>Journal of Crystal Growth</i> , <b>2018</b> , 499, 85-89	1.6	2
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142	Nonpolar GaN-Based Superluminescent Diode with 2.5 GHz Modulation Bandwidth <b>2018</b> ,		2
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129	Semipolar group III-nitride distributed-feedback blue laser diode with Indium tin oxide surface grating <b>2020</b> ,		2



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109	Hybrid MOCVD/MBE GaN tunnel junction LEDs with greater than 70% wall plug efficiency <b>2016</b> ,		1
108	High-speed performance of III-nitride 410 nm ridge laser diode on (202 1 ) plane for visible light communication <b>2016</b> ,		1
107	Nonpolar GaN-based vertical-cavity surface-emitting lasers <b>2017</b> ,		1
106	Integrated photonic platform based on semipolar InGaN/GaN multiple section laser diodes <b>2017</b> ,		1
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104	InGaN-Based Solar Cells and High-Performance Broadband Optical Coatings for Ultrahigh Efficiency Hybrid Multijunction Device Designs <b>2013</b> ,		1
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